RENESAS

HD74LV1GW97A

Configurable Multiple–Function Gate

REJ03D0083-0300 Rev.3.00 May 19, 2006

Description

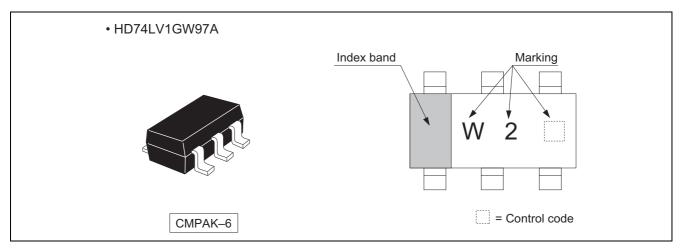
The HD74LV1GW97A has configurable multiple–function gate in a 6 pin package. The Output state is determined by eight patterns of 3–bit input. The user can choose the logic functions AND, NAND, OR, NOR, INVERTER, Non–Invert Buffer, Data Selector. Low voltage and high-speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

Features

- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- Supply voltage range : 1.65 to 5.5 V Operating temperature range : -40 to +85°C
- All inputs V_{IH} (Max.) = 5.5 V (@V_{CC} = 0 V to 5.5 V) All outputs V_0 (Max.) = 5.5 V (@V_{CC} = 0 V)
- Output current $\pm 6 \text{ mA}$ (@V_{CC} = 3.0 V to 3.6 V), $\pm 12 \text{ mA}$ (@V_{CC} = 4.5 V to 5.5 V)
- All the logical input has hysteresis voltage for the slow transition.
- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LV1GW97ACME	CMPAK-6 pin	PTSP0006JA-A (CMPAK-6V)	СМ	E (3,000 pcs / Reel)

Outline and Article Indication





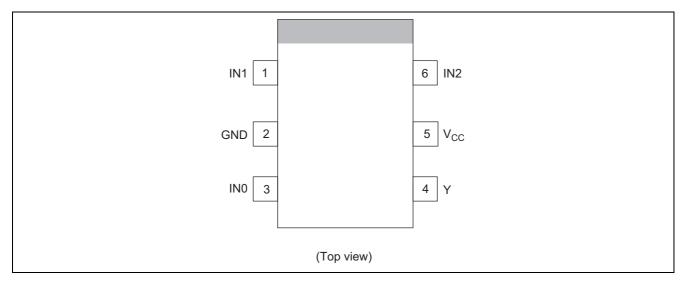
Function Table

	Inputs		Output
IN2	IN1	INO	Y
L	L	L	L
L	L	Н	L
L	Н	L	н
L	Н	Н	н
Н	L	L	L
Н	L	Н	н
Н	Н	L	L
Н	Н	Н	Н

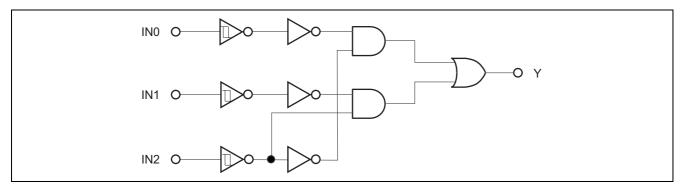
H : High level

L : Low level

Pin Arrangement



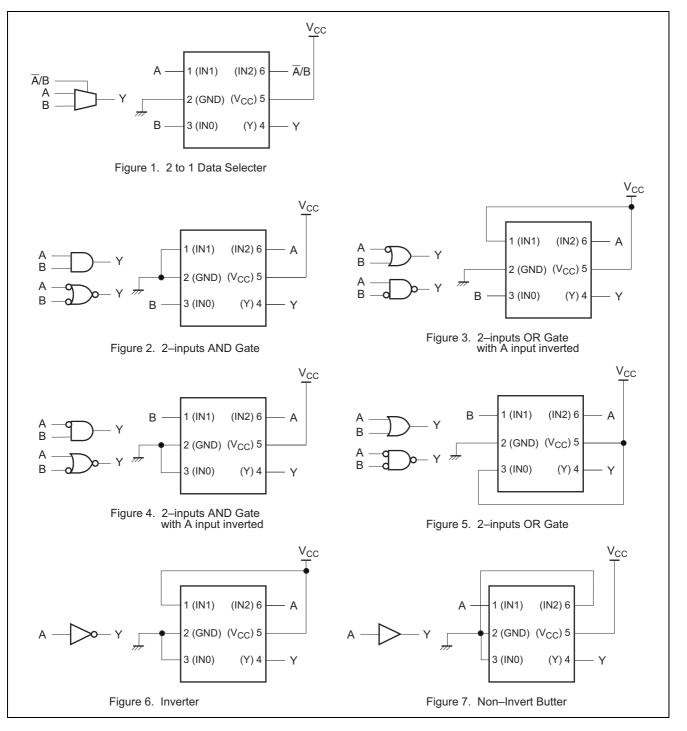
Logic Diagram

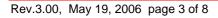


Function Selection Table

Logic Function	Figure No.
2 to 1 data Selector	1
2–inputs AND	2
2-inputs OR with one input inverted	3
2-inputs NAND with one input inverted	3
2-inputs AND with one input inverted	4
2-inputs NOR with one input inverted	4
2–inputs OR	5
Inverter	6
Non–Inverter Buffer	7

Logic Configurations







Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V _{cc}	-0.5 to 7.0	V	
Input voltage range ^{*1}	VI	-0.5 to 7.0	V	
Output voltage range *1, 2	. V	-0.5 to V _{CC} + 0.5	V	Output : H or L
Output voltage lange	Vo	-0.5 to 7.0	- v	V _{CC} : OFF
Input clamp current	I _{IK}	-20	mA	V ₁ < 0
Output clamp current	Ι _{ΟΚ}	±50	mA	$V_0 < 0 \text{ or } V_0 > V_{CC}$
Continuous output current	Io	±25	mA	$V_{\rm O} = 0$ to $V_{\rm CC}$
Continuous current through V _{CC} or GND	I _{CC} or I _{GND}	±50	mA	
Maximum power dissipation at Ta = 25° C (in still air) ^{*3}	PT	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V _{cc}	1.65	5.5	V	
Input voltage range	VI	0	5.5	V	
Output voltage range	Vo	0	V _{CC}	V	
		—	1		V _{CC} = 1.65 to 1.95 V
	Let.	—	2		V_{CC} = 2.3 to 2.7 V
	lol	—	6		V_{CC} = 3.0 to 3.6 V
		—	12	- mA	V_{CC} = 4.5 to 5.5 V
Output current	Іон	—	-1		V_{CC} = 1.65 to 1.95 V
		—	-2		V_{CC} = 2.3 to 2.7 V
			-6		V_{CC} = 3.0 to 3.6 V
			-12		V_{CC} = 4.5 to 5.5 V
		0	300		V _{CC} = 1.65 to 1.95 V
anut transition rise or fall rate	A# / A	0	200	ns / V	V _{CC} = 2.3 to 2.7 V
nput transition rise or fall rate	$\Delta t / \Delta v$	0	100	ns/v	V_{CC} = 3.0 to 3.6 V
		0	20		V_{CC} = 4.5 to 5.5 V
Operating free-air temperature	Ta	-40	85	°C	

Note: Unused or floating inputs must be held high or low.



Electrical Characteristics

Ta = -40 to $85^{\circ}C$

Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	Test condition
		1.65 to 1.95	—	_	V _{CC} ×0.75		
	v +	2.5	—	_	1.75	1	
	V _T ⁺	3.3			2.31		
		5.0			3.50		
		1.65 to 1.95	V _{CC} ×0.25	_	_		
Threshold	V -	2.5	0.75	_			
voltage	V _T ⁻	3.3	0.99	_	_	V	
		5.0	1.5	_	_		
		1.65 to 1.95	0.1	_	V _{CC} ×0.4		
	ΔV_T	2.5	0.25	_	1.0]	
		3.3	0.33	_	1.32		
		5.0	0.5	_	2.0		
		Min to Max	V _{cc} -0.1		—		I _{OH} = -50 μA
		1.65	1.4		—		$I_{OH} = -1 \text{ mA}$
	V _{OH}	2.3	2.0		—		$I_{OH} = -2 \text{ mA}$
		3.0	2.48		—		I _{OH} = -6 mА
Output voltage		4.5	3.8		—	v	I _{OH} = -12 mA
Oulput voltage		Min to Max	—		0.1	v	I _{OL} = 50 μA
		1.65	—		0.3		I _{OL} = 1 mA
	V _{OL}	2.3	—		0.4		$I_{OL} = 2 \text{ mA}$
		3.0	—		0.44		$I_{OL} = 6 \text{ mA}$
		4.5	—		0.55		I _{OL} = 12 mA
Input current	l _{in}	0 to 5.5	—	_	±1	μA	$V_{IN} = 5.5 \text{ V or GND}$
Quiescent supply current	Icc	5.5	_	_	10	μA	$V_{IN} = V_{CC} \text{ or } GND,$ $I_{O} = 0$
Output leakage current	IOFF	0	—	_	5	μΑ	V_{IN} or $V_O = 0$ to 5.5 V
Input capacitance	CIN	3.3	—	3.0	_	pF	$V_{IN} = V_{CC}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.



Switching Characteristics

 $V_{CC} = 1.8 \pm 0.15 \text{ V}$

ltem	Symbol		Ta = 25°C	;	Ta = -40	to 85°C	Unit	Test	FROM	то
nem	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation	t _{PLH}		15.8	29.4	1.0	33.0		C∟ = 15 pF	IN	V
delay time	t _{PHL}		22.6	40.9	1.0	45.0	ns	C _L = 50 pF		T

 $V_{CC} = 2.5 \pm 0.2 V$

Item	Symbol		Ta = 25°C	Ta = -40 to 85°C		Unit Test		FROM	то	
nem	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation	t _{PLH}		9.4	17.6	1.0	21.0	ns	C _L = 15 pF	IN	Y
delay time	t _{PHL}		12.6	22.6	1.0	26.5		C _L = 50 pF	IIN	

 $V_{CC} = 3.3 \pm 0.3 V$

Item	Symbol	•	Ta = 25°C	;	Ta = -40) to 85°C	Unit	Test	FROM	то
item	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation	t _{PLH}		7.0	11.0	1.0	13.0	ns	C _L = 15 pF	IN	Y
delay time	t _{PHL}	_	9.5	14.5	1.0	16.5	-	C _L = 50 pF	11N	

 $V_{CC} = 5.0 \pm 0.5 V$

Item	Symbol	Ta = 25°C			Ta = -40 to 85°C		Unit	Test	FROM	то
nem	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation	t _{PLH}	—	4.8	6.8	1.0	8.0	nc	C∟ = 15 pF	IN	Y
delay time	t _{PHL}	_	6.3	8.8	1.0	10.0	ns	C _L = 50 pF		

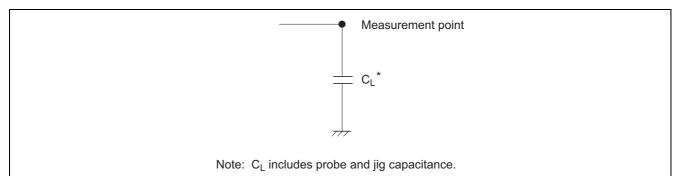
Operating Characteristics

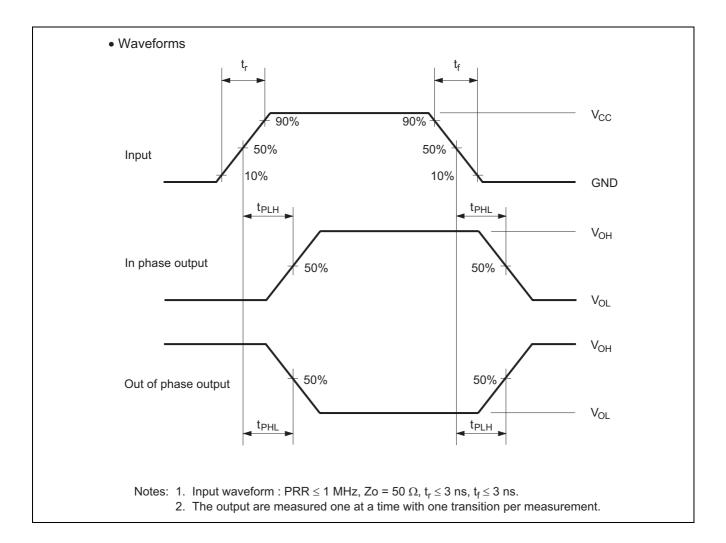
 $C_L = 50 \text{ pF}$

ltem	Symbol			Ta = 25°C		Unit	Test Conditions	
	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	Test Conditions	
Power dissipation	C	3.3		8.5		pF	f = 10 MHz	
capacitance		5.0		10.0	—	рг		



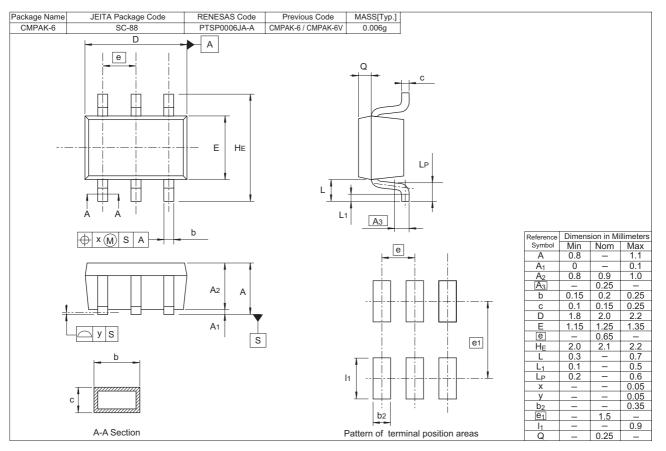
Test Circuit







Package Dimensions





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